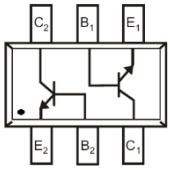
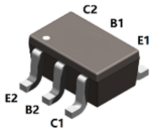
MMDT5551

Dual Bipolar Transistor(NPN+NPN)

Features

- Epitaxial planar die construction
- Complementary PNP type available(MMDT5401)





SOT-363

Mechanical Data

- Case: SOT-363
- Molding compound: UL flammability classification rating 94V-0
- Terminals: Tin-plated; solderability per MIL-STD-202, Method 208

Ordering Information

Part Number	Package	Shipping Quantity	Marking Code
MMDT5551	SOT-363	3000 pcs / Tape & Reel	K4N

Maximum Ratings (@ T_A = 25°C unless otherwise specified)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	180	V
Collector-Emitter Breakdown Voltage	V_{CEO}	160	V
Emitter-Base Breakdown Voltage	V_{EBO}	6	V
Collector Current (Continuous)	I_C	0.6	A
Collector Current (Peak)	I_{CM}	0.8	A

Thermal Characteristics

Parameter	Symbol	Value	Unit
Power Dissipation	P_D	0.2	W
Thermal Resistance Junction-to-Air	$R_{\theta JA}$	625	°C/W
Thermal Resistance Junction-to-Air *1	$R_{\theta JA}$	324	°C/W
Thermal Resistance Junction-to-Case *1	$R_{\theta JC}$	196	°C/W
Thermal Resistance Junction-to-Lead *1	$R_{\theta JL}$	214	°C/W
Junction Temperature Range	T_J	-55 ~ +150	°C
Storage Temperature Range	T_{STG}	-55 ~ +150	°C

Note 1: The data tested by surface mounted on a 1 inch^2 FR-4 board with 2OZ copper

Electrical Characteristics (@ T_A = 25°C unless otherwise specified)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	I_C = 100μA, I_E = 0	180	-	-	V
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	I_C = 1mA, I_B = 0	160	-	-	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	I_E = 10μA, I_C = 0	6	-	-	V
Collector Cut-off Current	I_{CBO}	V_{CB} = 120V, I_E = 0	-	-	50	nA
Emitter Cut-off Current	I_{EBO}	V_{EB} = 4V, I_C = 0	-	-	50	nA
DC Current Gain	h_{FE}	V_{CE} = 5V, I_C = 1mA	80	-	-	-
		V_{CE} = 5V, I_C = 10mA	100	-	300	-
		V_{CE} = 5V, I_C = 50mA	30	-	-	-
Collector-emitter Saturation Voltage	$V_{CE(sat)}$	I_C = 10mA, I_B = 1mA	-	-	0.15	V
		I_C = 50mA, I_B = 5mA	-	-	0.2	V
Base-emitter Saturation Voltage	$V_{BE(sat)}$	I_C = 10mA, I_B = 1mA	-	-	1	V
		I_C = 50mA, I_B = 5mA	-	-	1	V
Collector-base Output Capacitance	C_{cbo}	V_{CB} = 10V, f = 1MHz, I_E = 0	-	-	6	pF
Current-Gain— Bandwidth Product	f_T	I_C = 10mA, V_{CE} = 10V f = 100MHz	100	-	300	MHz

Ratings and Characteristics Curves (@ T_A = 25°C unless otherwise specified)

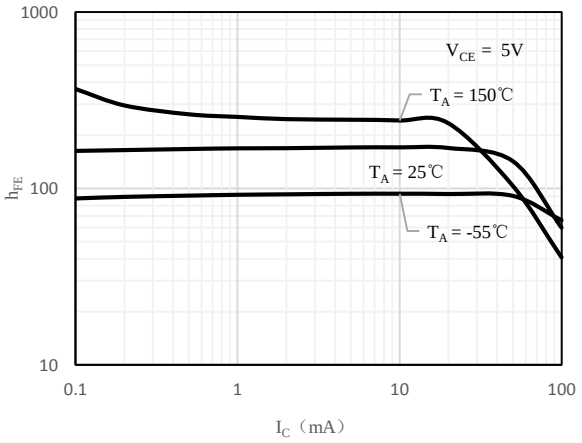


Fig 1 h_{FE} vs. I_C

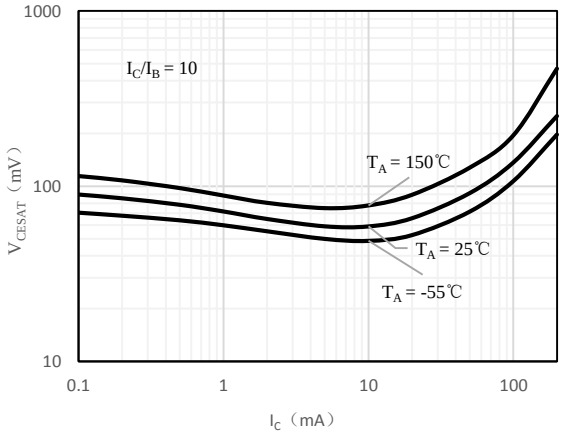


Fig 2 $V_{CE(sat)}$ vs. I_C

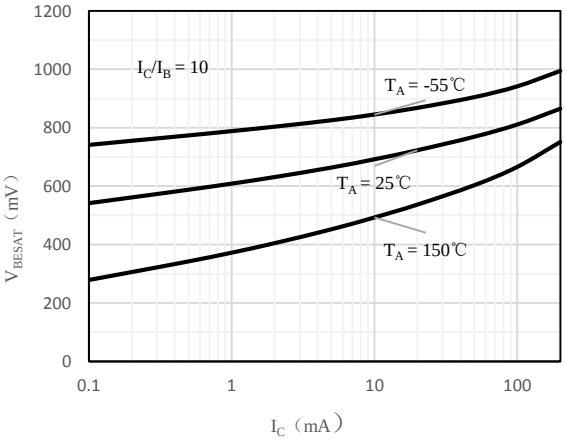


Fig 3 $V_{BE(sat)}$ vs. I_C

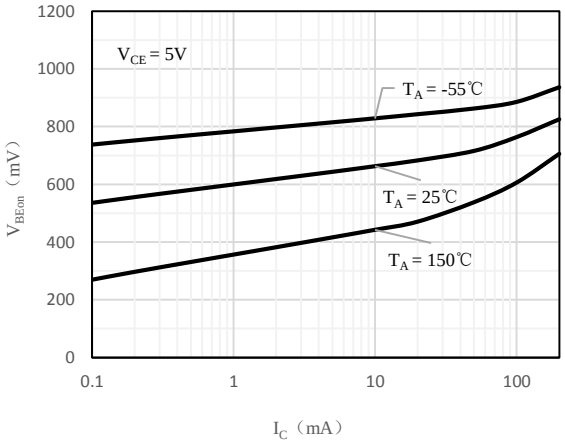


Fig 4 $V_{BE(ON)}$ vs. I_C

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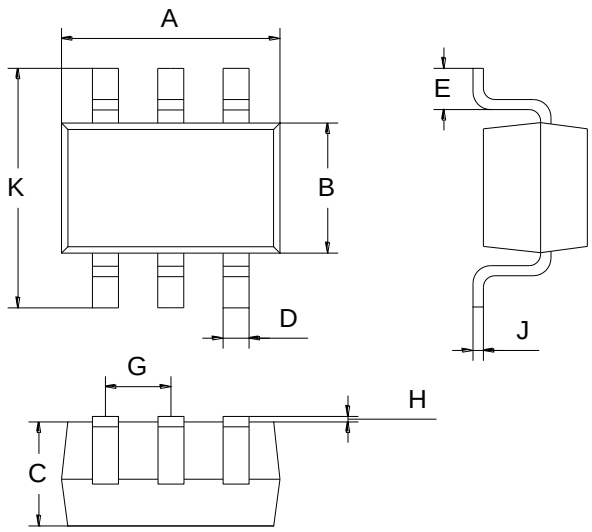
Package Outline Dimensions (Unit: mm)



Mounting Pad Layout (Unit: mm)

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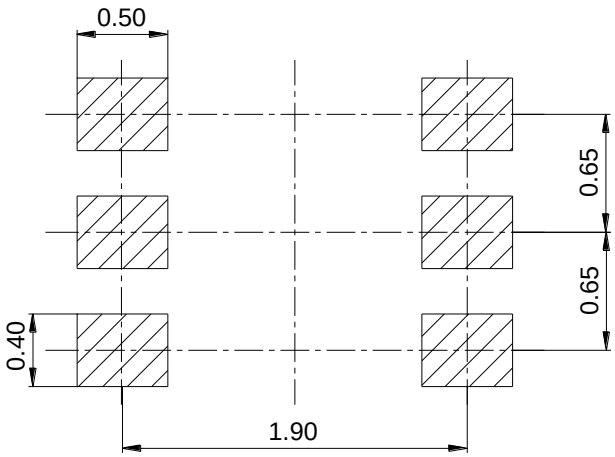

Package	Reel	Reel Size	Box	Box Size(mm)	Carton	Carton Size(mm)
SOT-363	3000pcs	7inch	45,000pcs	203×203×195	180,000pcs	438×438×220